

Product Change Notification



Product Group: Vishay Siliconix/May 23, 2014/PCN-SIL-0102014 Rev 1

Qualification of ASE as an Additional Assembly Site of TO-220 Commercial Power Mosfets

DESCRIPTION OF CHANGE: Vishay Siliconix would like to announce the approval of Advanced Semiconductor Engineering (ASE) plant located in Weihai, China as an additional assembly facility for TO-220, MOSFET devices.

ASE Weihai has provided world-class total manufacturing services since Q1 2008, and has received international quality systems and environmental compliance certifications TS16949, ISO9001, ISO14001 and OSHAS 18001.

This facility will join the current Vishay-Siliconix qualified facilities, in providing additional capacity for MOSFETs built in the TO-220 package. The manufacturing process to be used in ASE will be similar to that used in the Xi'an facility. No electrical changes in the device are expected.

Additionally, there will be slight modifications to the mechanical dimensions of the TO-220 Package Outline. The updated TO-220 package outline drawing is exhibited below in this PCN.

Rev 1 of this PCN removes the Package Outline Drawing (POD) modification. Parts built in ASE will be in compliance to JEDEC outline drawing TO-220AB.

CLASSIFICATION OF CHANGE: Manufacturing Expansion

REASON FOR CHANGE: Increased capacity, additional source.

EXPECTED INFLUENCE ON QUALITY/RELIABILTY/PERFORMANCE: None

PRODUCT CATAGORY: MOSFET

PART NUMBERS/SERIES/FAMILIES AFFECTED: Refer to list of active part numbers included with this PCN

VISHAY BRAND(s): Vishay-Siliconix

TIME SCHEDULE: Shipment of production volumes will begin August 23, 2014.

SAMPLE AVAILABILITY: Please refer to the list below for the parts that will be built for sampling to customers. Please contact your regional Vishay Sales office for sample ordering.

PRODUCT IDENTIFICATION: TO-220 products manufactured in ASE will have part marking in the form of **N46K** where the **N** is the factory designator for ASE.

QUALIFICATION DATA: Please contact your local sales office for a copy of the qualification report.

This PCN is considered approved, without further notification, unless we receive specific customer concerns before August 23, 2014 or as specified by contract.

ISSUED BY: Don Larson, Vishay Siliconix, Technical Marketing Manager.

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Vishay Intertechnology, Inc.



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Affected Parts

Part Number					
IRF510PBF	IRF730PBF	IRF9630PBF	IRFZ10PBF	IRLZ34PBF	
IRF520PBF	IRF740BPBF	IRF9Z10PBF	IRFZ14PBF	SIHP10N40D-E3	
IRF530PBF	IRF820APBF	IRF9Z14PBF	IRFZ20PBF	SIHP10N40D-GE3	
IRF610PBF	IRF820PBF	IRF9Z20PBF	IRFZ24PBF	SIHP5N50D-E3	
IRF614PBF	IRF830APBF	IRF9Z24PBF	IRFZ30PBF	SIHP5N50D-GE3	
IRF620PBF	IRF830BPBF	IRF9Z30PBF	IRFZ34PBF	SIHP6N40D-E3	
IRF624PBF	IRF830PBF	IRF9Z34PBF	IRL510PBF	SIHP6N40D-GE3	
IRF630PBF	IRF840BPBF	IRFBC20PBF	IRL520PBF	SIHP8N50D-E3	
IRF634PBF	IRF9510PBF	IRFBC30APBF	IRL530PBF	SIHP8N50D-GE3	
IRF710PBF	IRF9520PBF	IRFBC30PBF	IRL620PBF		
IRF720PBF	IRF9530PBF	IRFBE20PBF	IRL630PBF		
IRF730APBF	IRF9610PBF	IRFBF20PBF	IRLZ14PBF		
IRF730BPBF	IRF9620PBF	IRFBG20PBF	IRLZ24PBF		

Samples

The following parts are planned to be built for sampling:

Part Number								
IRF510PBF	IRF730PBF	IRF840BPBF						
IRF520PBF	IRF740BPBF	IRF9630PBF						
IRF530PBF	IRF820PBF	IRFBC20PBF						
IRF610PBF	IRF830PBF	IRFBG20PBF						



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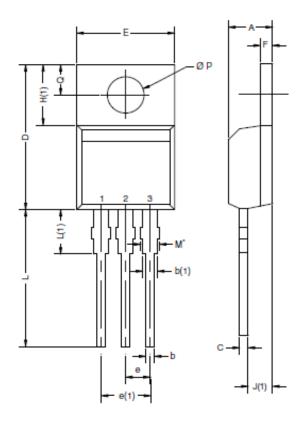
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Outline Drawing

DIM (inches)	JEDEC		Current		Revised (Updates in BOLD)		Change
	Min.	Max.	Min.	Max.	Min.	Max.	
Α	0.140	0.190	0.167	0.183	0.163	0.185	-0.004/+0.002
b	0.015	0.040	0.027	0.040	0.027	0.040	None
b(1)	0.045	0.070	0.047	0.068	0.045	0.068	-0.02
С	0.014	0.024	0.014	0.024	0.014	0.024	None
D	0.560	0.650	0.585	0.610	0.564	0.624	-0.021/+0.014
E	0.380	0.420	0.395	0.414	0.392	0.414	-0.003
e	0.100 BSC		0.095	0.105	0.095	0.105	None
e(1)	0.200 BSC		0.192	0.208	0.192	0.208	None
F	0.020	0.055	0.045	0.055	0.017 0.020	0.055	-0.028
H(1)	0.230	0.270	0.240	0.255	0.240	0.264	+0.009
J(1)	0.080	0.115	0.095	0.115	0.095	0.115	None
L	0.500	0.580	0.526	0.552	0.526	0.567	+0.015
L(1)		0.250	0.131	0.150	0.131	0.159	+0.009
¢Р	0.139	0.161	0.139	0.155	0.139	0.155	None
Q	0.100	0.116	0.102	0.118	0.100	0.118	-0.002
*M	None		0.052	0.064	0.052	0.064	None

Notes:

- 1. M = 0.052 to 0.064 inches (dimension including protrusion) Heatsink hole for HVM.
- 2. Outline conforms to JEDEC outline TO-220 AB with exception of dimension F.



Vishay Intertechnology, Inc.

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